

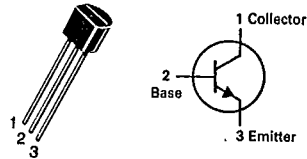
MAXIMUM RATINGS

Rating	Symbol	BC 485	BC 487	BC 489	Unit
Collector-Emitter Voltage	V_{CEO}	45	60	80	Vdc
Collector-Base Voltage	V_{CBO}	45	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	5.0			Vdc
Collector Current - Continuous	I_C	0.5			Adc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625	5.0		mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5	12		Watt mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150			$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$

BC485, A, B, L
BC487, A, B, L
BC489, A, B, L

 CASE 29-04, STYLE 17
 TO-92 (TO-226AA)


HIGH CURRENT TRANSISTORS

NPN SILICON

Refer to MPSA05 for graphs.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage* ($I_C = 10\text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	45 60 80	— — —	— — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\text{ }\mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	45 60 80	— — —	— — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current $V_{CB} = 30\text{ Vdc} - I_E = 0$ BC485 $V_{CB} = 40\text{ Vdc} - I_E = 0$ BC487 $V_{CB} = 60\text{ Vdc} - I_E = 0$ BC489	I_{CBO}	— — —	— — —	100 100 100	nAdc

ON CHARACTERISTICS*

DC Current Gain ($I_C = 10\text{ mAdc} - V_{CE} = 2.0\text{ Vdc}$) ($I_C = 100\text{ mAdc} - V_{CE} = 2.0\text{ Vdc}$)	h_{FE}	40			
BC485/487/489		60		400	
BC485L/487L/489L		60	120	150	
BC485A/487A/489A		100	160	250	
BC485B/487B/489B		160	260	400	
($I_C = 1\text{ Adc} - V_{CE} = 5.0\text{ Vdc}$)*		15			
Collector Emitter Saturation Voltage ($I_C = 500\text{ mAdc} - I_B = 50\text{ mAdc}$) ($I_C = 1\text{ Adc} - I_B = 100\text{ mAdc}$)	$V_{CE(sat)}$	— —	0.2 0.3	0.50 —	Vdc
Base Emitter Saturation Voltage ($I_C = 500\text{ mAdc}, I_B = 50\text{ mAdc}$) ($I_C = 1\text{ Adc} - I_B = 100\text{ mAdc}$)*	$V_{BE(sat)}$	—	0.85 0.90	1.20	Vdc

DYNAMIC CHARACTERISTICS

Current-Gain-Bandwidth Product ($I_C = 50\text{ mAdc}, V_{CE} = 2.0\text{ Vdc}, f = 100\text{ MHz}$)	f_T	—	200	—	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}, I_E = 0, f = 1.0\text{ MHz}$)	C_{ob}	—	7	—	pF
Input Capacitance ($V_{BE} = 0.5\text{ Vdc}, I_C = 0, f = 1.0\text{ MHz}$)	C_{ib}	—	50	—	pF

* Pulse test - Pulse width = 300 μs - Duty Cycle 2%.